

The S-5470 Series, developed by CMOS technology, is a normally-off faint signal detection IC with an ultra-low current consumption.

This IC has a function to detect certain current level of 0.7 nA typ., which makes it possible to detect faint signals for a variety of electric generating devices or sensor devices. It also has a function to detect the difference of current level, and thus detects difference between strengths of two signals input at the same time.

Due to its ultra-low current consumption and low-voltage operation, the S-5470 Series is suitable for battery-operated small mobile device applications.

■ Features

- Ultra-low current consumption: $I_{DD} \leq 0.1$ nA typ.
- Faint current detection: $I_{DET} = 0.7$ nA typ.
- Wide operation voltage range: $V_{DD} = 0.9$ V to 5.5 V
- Detection of faint signal: Detects faint signals of approximately 0.7 nW (1.0 V, 0.7 nA typ.)
- Detection of signal strength difference: Detects difference between strengths of two signals input at the same time
- Lead-free (Sn 100%), halogen-free

■ Applications

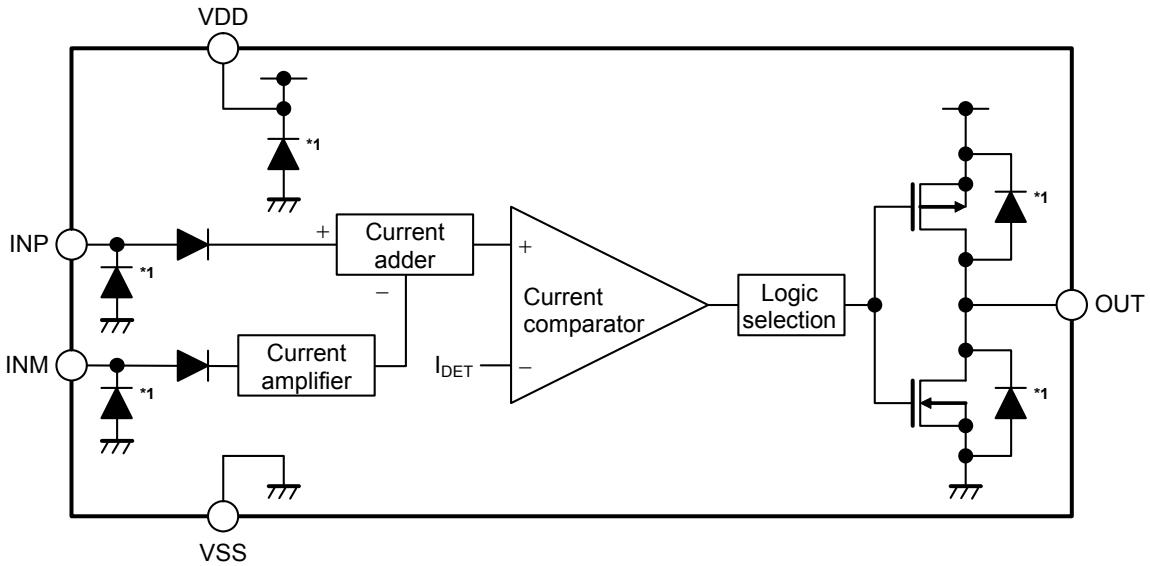
- Detects output signals of electric generating devices or sensor devices with high internal resistance
- Advanced sensing using two electric generating devices or sensor devices
- Miniaturization and low power consumption for various sensors of portable and wireless devices

■ Package

- SOT-23-5

■ Block Diagrams

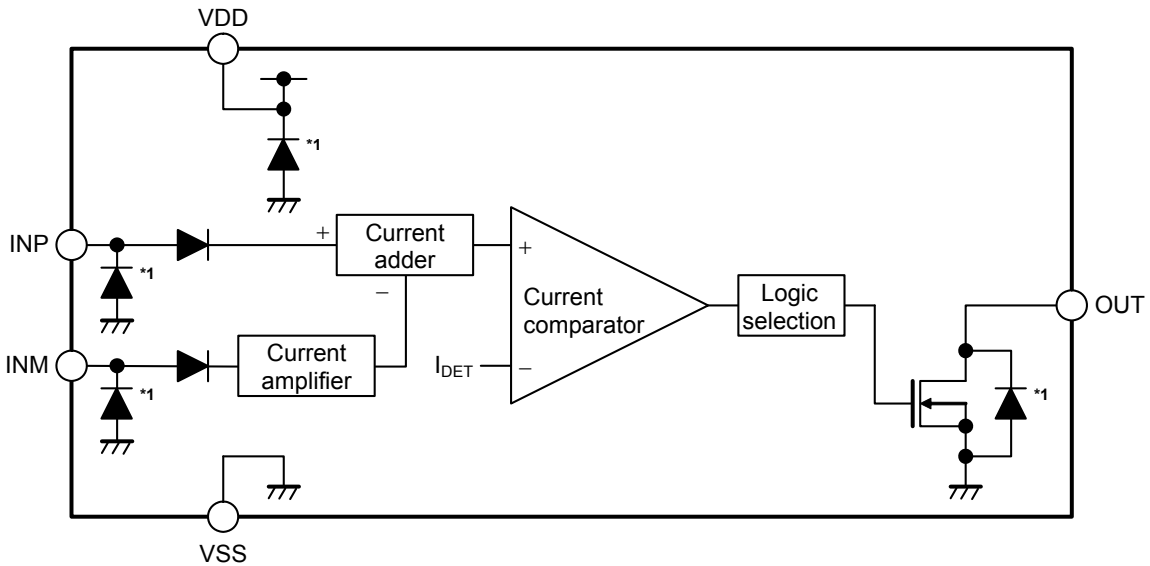
1. CMOS output product



*1. Parasitic diode

Figure 1

2. Nch open-drain output product



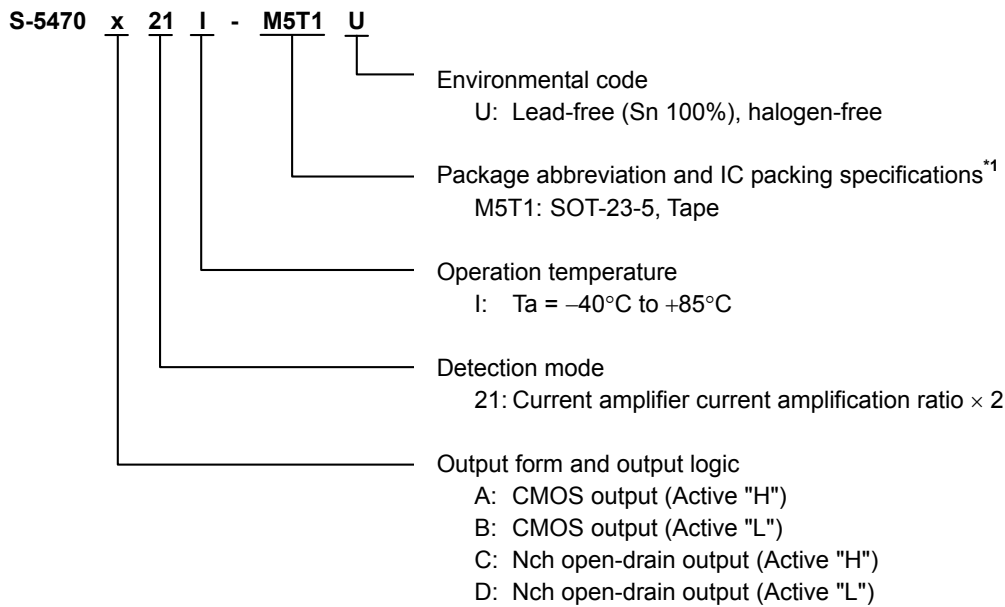
*1. Parasitic diode

Figure 2

■ Product Name Structure

Users can select the output form and output logic for the S-5470 Series. Refer to "1. Product name" regarding the contents of the product name, "2. Package" regarding the package drawings, "3. Product name list" regarding details of the product name.

1. Product name



*1. Refer to the tape drawing.

2. Package

Table 1 Package Drawing Codes

Package Name	Dimension	Tape	Reel
SOT-23-5	MP005-A-P-SD	MP005-A-C-SD	MP005-A-R-SD

3. Product name list

Table 2

Product Name	Output Form	Output Logic	Detection Mode
S-5470A21I-M5T1U	CMOS output	Active "H"	Current amplifier current amplification ratio × 2
S-5470B21I-M5T1U	CMOS output	Active "L"	Current amplifier current amplification ratio × 2
S-5470C21I-M5T1U	Nch open-drain output	Active "H"	Current amplifier current amplification ratio × 2
S-5470D21I-M5T1U	Nch open-drain output	Active "L"	Current amplifier current amplification ratio × 2

Remark Please contact our sales office for products other than the above.

■ Pin Configuration

1. SOT-23-5

Top view

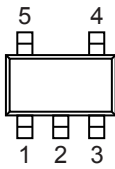


Figure 3

Table 3

Pin No.	Symbol	Description
1	VDD	Power supply pin
2	VSS	GND pin
3	INM	Reference current input pin
4	INP	Detection current input pin
5	OUT	Output pin

■ Absolute Maximum Ratings

Table 4

(Ta = +25°C unless otherwise specified)

Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltage	V _{DD}	V _{SS} - 0.3 to V _{SS} + 7.0	V
Input voltage	V _{INP} , V _{INM}	V _{SS} - 0.3 to V _{SS} + 7.0	V
Output voltage	CMOS output product	V _{SS} - 0.3 to V _{DD} + 0.3	V
	Nch open-drain output product	V _{SS} - 0.3 to V _{SS} + 7.0	V
Output pin current	I _{SOURCE}	20	mA
	I _{SINK}	20	mA
Power dissipation	P _D	600 ^{*1}	mW
Operation ambient temperature	T _{opr}	-40 to +85	°C
Storage temperature	T _{stg}	-55 to +125	°C

*1. When mounted on board
 [Mounted board]

- (1) Board size: 114.3 mm × 76.2 mm × t1.6 mm
- (2) Name: JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

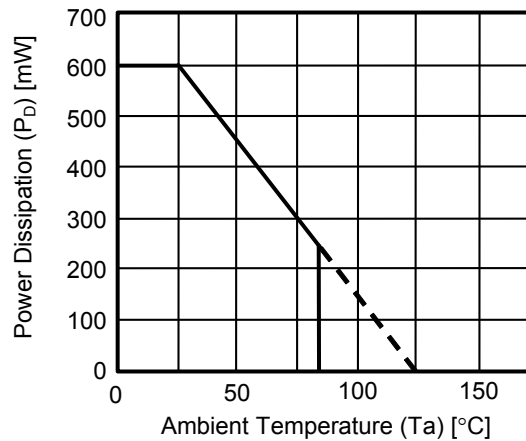


Figure 4 Power Dissipation of Package (When Mounted on Board)

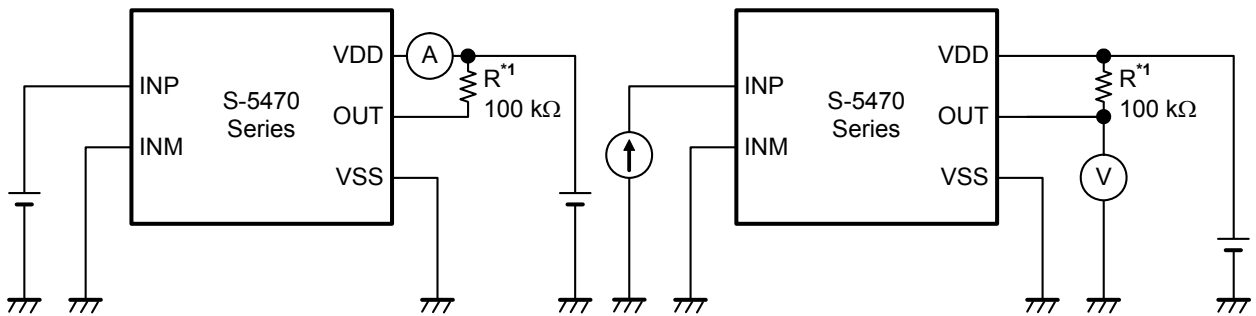
■ Electrical Characteristics

Table 5

(Ta = +25°C, VDD = 3.0 V unless otherwise specified)

Item	Symbol	Condition	Min.	Typ.	Max.	Unit	Test Circuit	
Power supply voltage	V _{DD}	Ta = -40°C to +85°C	0.9	–	5.5	V	–	
Current consumption	I _{DD}	V _{INP} = V _{SS} , V _{INM} = V _{SS}	–	0.01	10	nA	1	
		V _{INP} = 1.0 V, V _{INM} = V _{SS}	–	0.02	10	nA	1	
Detection current	I _{DET}	–	0.52	0.7	0.88	nA	2	
Release current	I _{REL}	–	I _{DET} × 0.7	I _{DET} × 0.8	I _{DET} × 0.9	nA	2	
Detection current temperature coefficient	I _{tc}	Ta = -40°C to +85°C	–	±0.5	–	%/°C	–	
Input current	I _{INP}	V _{INP} = 1.0 V	20	–	–	μA	3	
	I _{INM}	V _{INM} = 1.0 V	10	–	–	μA	3	
Current amplifier current amplification ratio × 2	G _{INM}	–	1.8	2.0	2.2	Times	4	
Source current	I _{SOURCE}	CMOS output product V _{OUT} = V _{DD} – 0.3 V	V _{DD} = 0.9 V	0.01	0.4	–	mA	5
			V _{DD} = 3.0 V	3.5	4.8	–	mA	5
Sink current	I _{SINK}	V _{OUT} = 0.3 V	V _{DD} = 0.9 V	0.5	1.7	–	mA	6
			V _{DD} = 3.0 V	7.0	9.2	–	mA	6
Output response time	t _{OD}	–	–	–	15	ms	–	

■ Test Circuits



*1. Resistor (R) is unnecessary for the CMOS output product.

*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 5 Test Circuit 1

Figure 6 Test Circuit 2

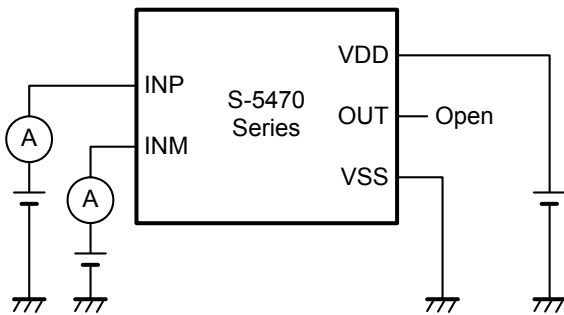
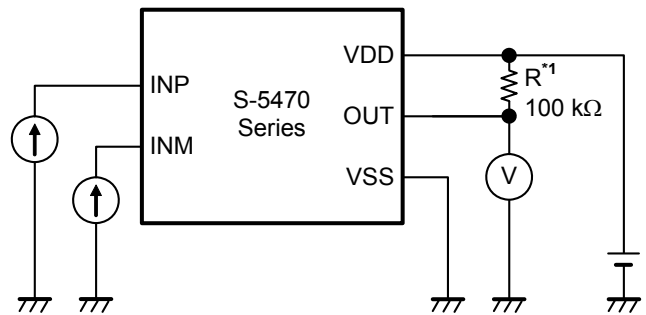


Figure 7 Test Circuit 3



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 8 Test Circuit 4

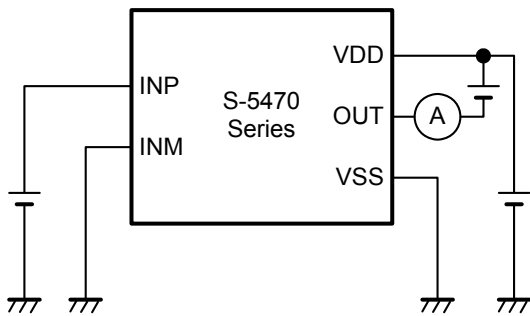


Figure 9 Test Circuit 5

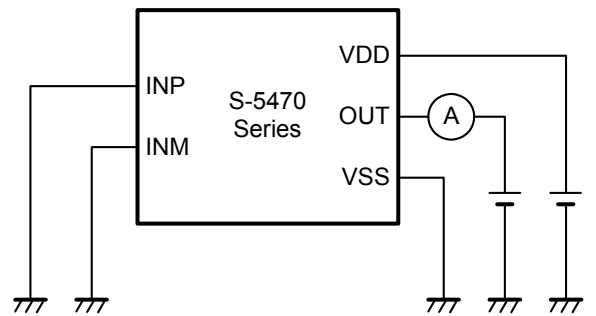
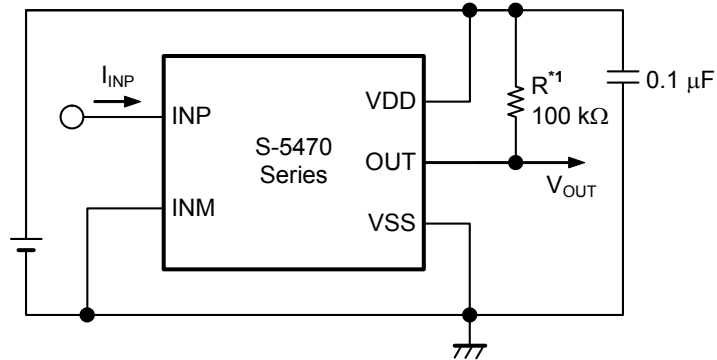


Figure 10 Test Circuit 6

■ **Standard Circuits**

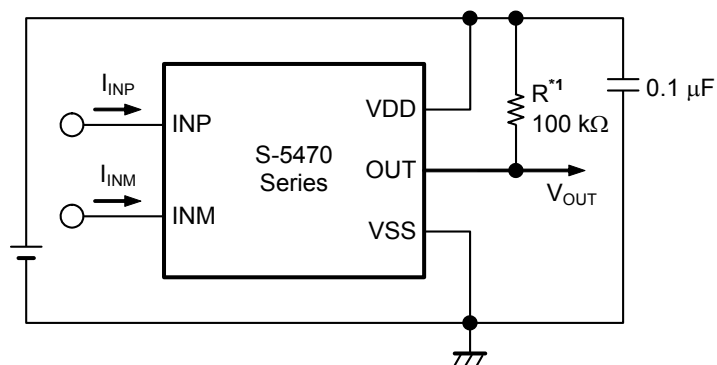
1. **Certain current level detector**



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 11

2. **Current level difference detector**



*1. Resistor (R) is unnecessary for the CMOS output product.

Figure 12

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

■ Operation

The S-5470 Series detects either certain current level or the difference of current level.

The operation of the S-5470 Series is described below, using CMOS output and active "H" products as examples.

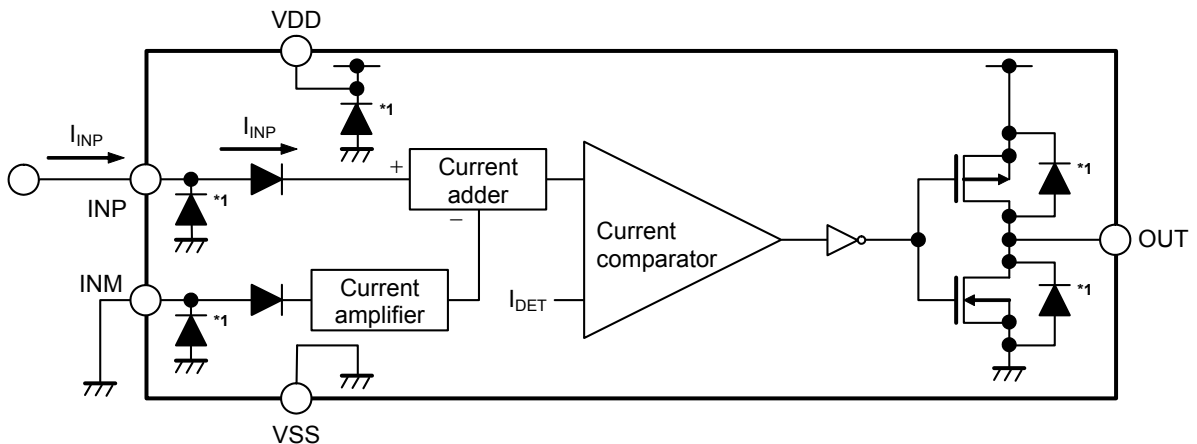
1. Basic operation when detecting certain current level (INM pin = V_{SS})

The S-5470 Series operates as follows when the INM pin is connected to V_{SS} pin.

- (1) If I_{INP} is lower than I_{DET}, an "L" level signal is output from the OUT pin.
- (2) If I_{INP} increases and becomes equal to or higher than I_{DET}, an "H" level signal is output from the OUT pin (point A in **Figure 14**). Even if I_{INP} decreases and falls below I_{DET}, as long as I_{INP} is higher than I_{REL}, an "H" level signal is output from the OUT pin.
- (3) If I_{INP} then decreases further and becomes equal to or lower than I_{REL}, an "L" level signal is output from the OUT pin (point B in **Figure 14**).

Remark I_{INP}: Current input to the INP pin
 I_{DET}: Detection current (refer to "4. 1 Detection current (I_{DET})")
 I_{REL}: Release current (refer to "4. 2 Release current (I_{REL})")

- Caution 1.** There are internal diodes at the INP pin and the INM pin. Therefore, in order to input a current to the INP pin and the INM pin, an input voltage of at least the forward voltage of these diodes is required.
- 2.** Feed-through current (I_{PEAK} = 100 nA) flows around the time when the OUT pin voltage switches, as shown in **Figure 14**. Therefore, if the input current is fixed around this time, the current consumption will increase.



*1. Parasitic diode

Figure 13 Diagram of the Operation when Detecting Certain Current Level

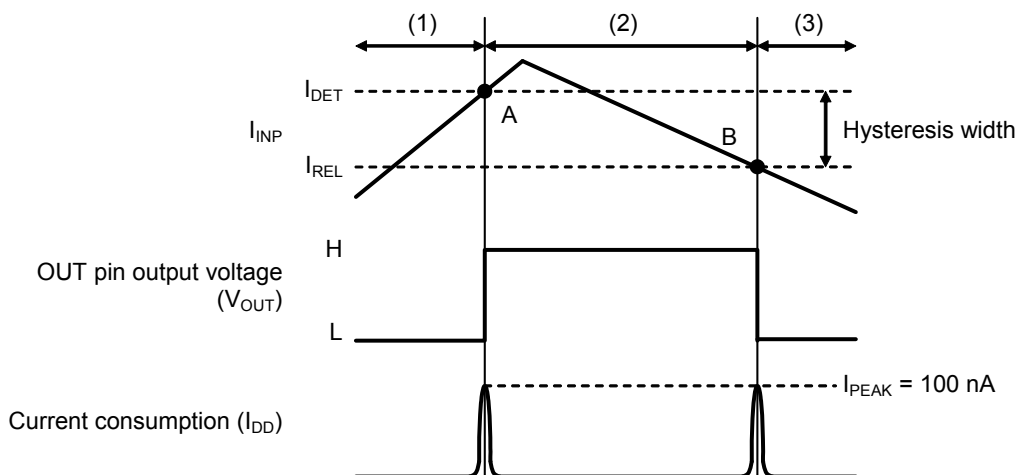


Figure 14 Operation when Detecting Certain Current Level
 ABLIC Inc.

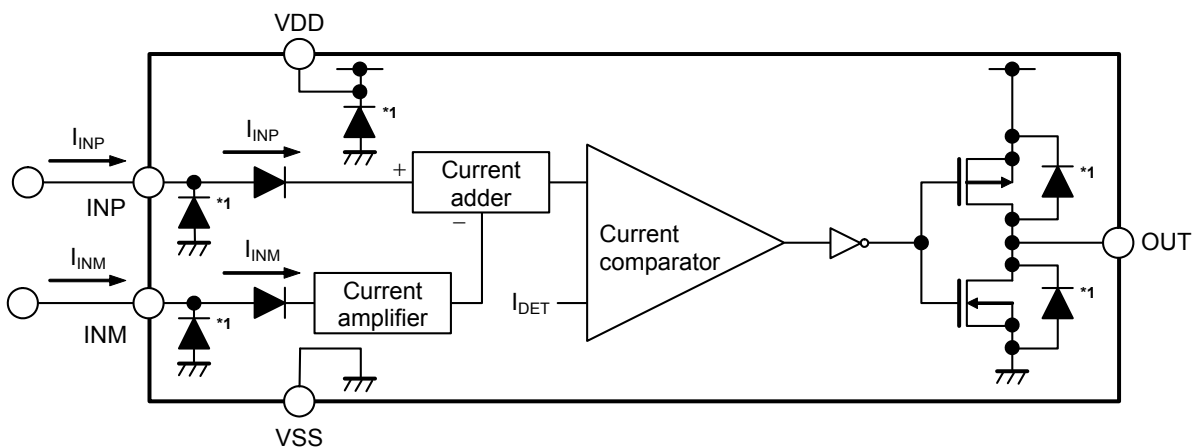
**2. Basic operation when detecting the difference of current level
 (Current amplifier current amplification ratio × G_{INM})**

The S-5470 Series operates as follows when current (I_{INM}) is applied to the INM pin.

- (1) If I_{INP} is lower than $I_{DET} + G_{INM} \times I_{INM}$, an "L" level signal is output from the OUT pin.
- (2) If I_{INP} increases and becomes equal to or higher than $I_{DET} + G_{INM} \times I_{INM}$, an "H" level signal is output from the OUT pin (point A in **Figure 16**). Even if I_{INP} decreases and falls below $I_{DET} + G_{INM} \times I_{INM}$, as long as I_{INP} is higher than $I_{REL} + G_{INM} \times I_{INM}$, an "H" level signal is output from the OUT pin.
- (3) If I_{INP} then decreases further and becomes equal to or lower than $I_{REL} + G_{INM} \times I_{INM}$, an "L" level signal is output from the OUT pin (point B in **Figure 16**).

Remark I_{INP} : Current input to the INP pin
 I_{INM} : Current input to the INM pin
 I_{DET} : Detection current (refer to "4. 1 Detection current (I_{DET})")
 I_{REL} : Release current (refer to "4. 2 Release current (I_{REL})")

- Caution 1.** There are internal diodes at the INP pin and the INM pin. Therefore, in order to input a current to the INP pin and the INM pin, an input voltage of at least the forward voltage of these diodes is required.
- 2.** Feed-through current ($I_{PEAK} = 100 \text{ nA}$) flows around the time when the OUT pin voltage switches, as shown in **Figure 16**. Therefore, if the input current is fixed around this time, the current consumption will increase.



*1. Parasitic diode

Figure 15 Diagram of the Operation when Detecting the Difference of Current Level

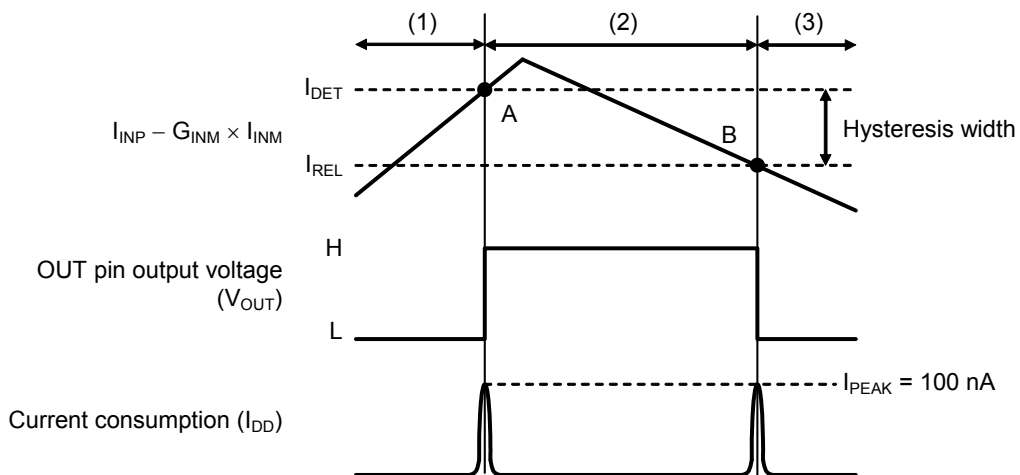
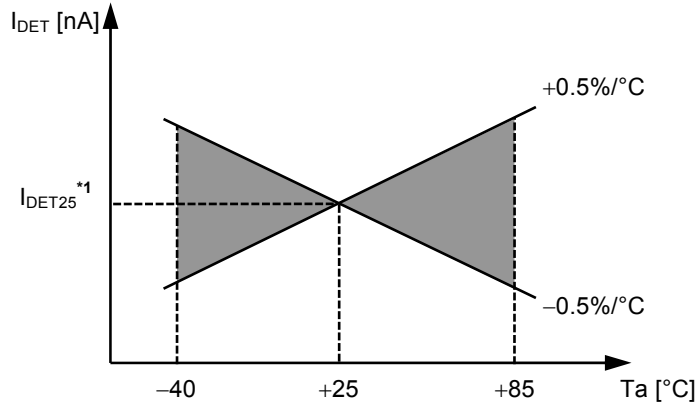


Figure 16 Operation when Detecting the Difference of Current Level

3. Temperature characteristics of detection current

The shaded area in **Figure 17** shows the temperature characteristics of the detection voltage in the operation temperature range.



*1. I_{DET25} : Detection current value at $T_a = +25^{\circ}\text{C}$

Figure 17 Temperature Characteristics of Detection Current

4. Explanation of terms

4.1 Detection current (I_{DET})

The detection current (I_{DET}) is the current at which the output switches to "H".

The detection current varies slightly even among products with the same specification. The variation in detection current from the minimum detection current ($I_{DET \text{ min.}}$) to the maximum detection current ($I_{DET \text{ max.}}$) is called the detection current range (refer to **Figure 18**).

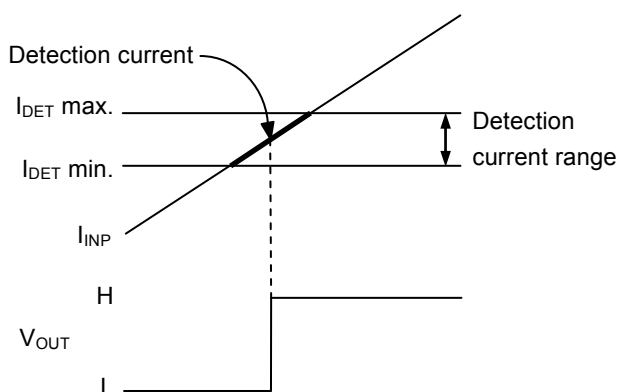


Figure 18 Detection Current

4.2 Release current (I_{REL})

The release current (I_{REL}) is the current at which the output switches to "L".

The release current varies slightly even among products with the same specification. The variation in release current from the minimum release current ($I_{REL \text{ min.}}$) to the maximum release current ($I_{REL \text{ max.}}$) is called the release current range (refer to **Figure 19**).

The range is calculated from the actual detection current (I_{DET}) of a product and is in the range of $I_{DET} \times 0.7 \leq I_{REL} \leq I_{DET} \times 0.9$.

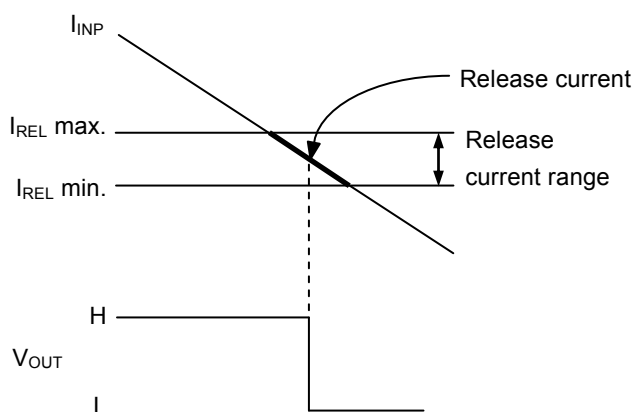


Figure 19 Release Current

4.3 Hysteresis width

The hysteresis width is the current difference between the detection current and the release current (current at point B – current at point A in "**Figure 14 Operation when Detecting Certain Current Level**" and "**Figure 16 Operation when Detecting the Difference of Current Level**").

The hysteresis width between the detection current and the release current prevents malfunction caused by noise in the input current.

■ Application Circuits

1. Certain photocurrent level detector

If PD or LED exceeds a certain value, the output signal inverts.

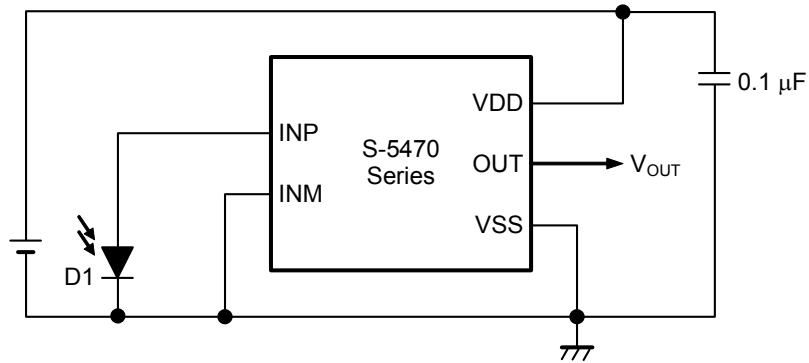


Figure 20 Example Certain Photocurrent Level Detector (CMOS Output Product)

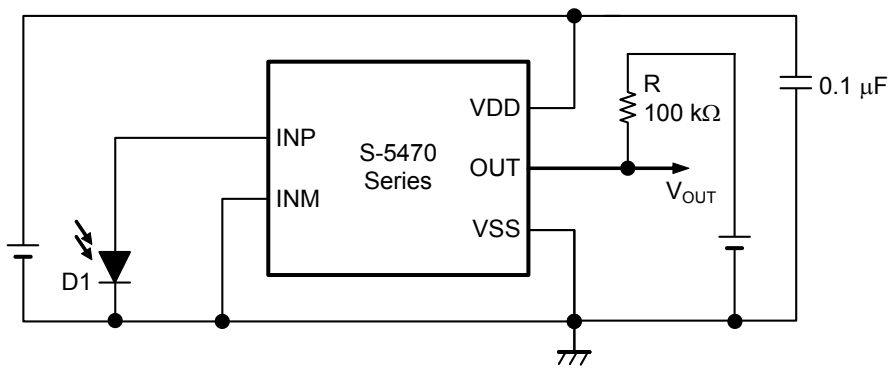


Figure 21 Example Certain Photocurrent Level Detector (Nch Open-drain Output Product)

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

2. Photocurrent level difference detector

If the difference in the photocurrent generated by the two PDs or the two LEDs exceeds a certain value, the output signal inverts.

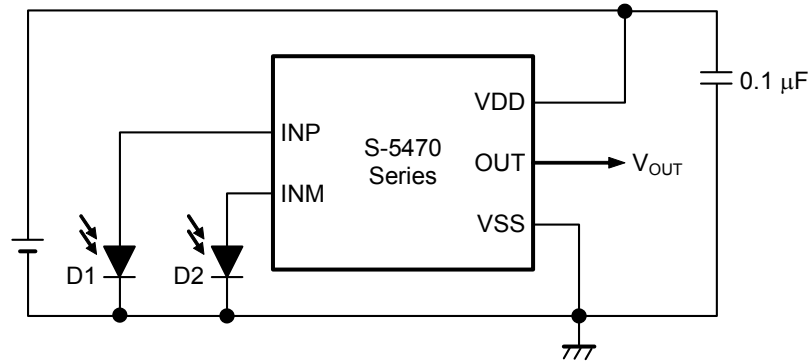


Figure 22 Example Photocurrent Level Difference Detector (CMOS Output Product)

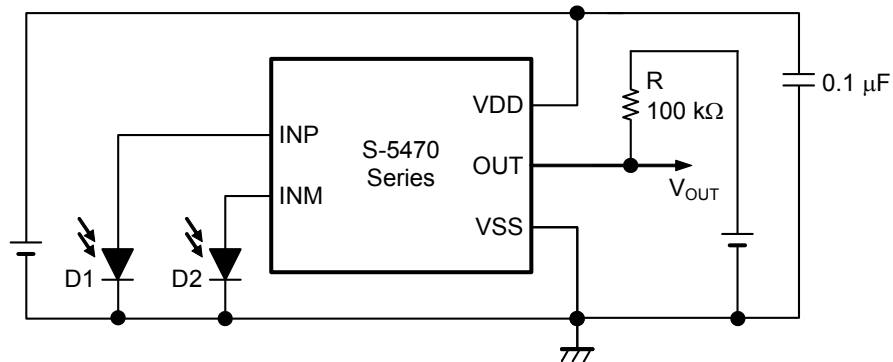


Figure 23 Example Photocurrent Level Difference Detector (Nch Open-drain Output Product)

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

3. Selection of PD or LED

Use PD or LED whose generation voltage is 1.0 V or more under usable light quantity.

Moreover, as for the test circuit shown in **Figure 24**, select PD or LED that satisfies the conditions below with detection or measurement of the quantity of light incidence in usage environment.

- Certain photocurrent level detector
 $I_{DET} \leq I$
- Photocurrent level difference detector
 $1 \text{ nA} \leq I \leq 20 \text{ } \mu\text{A}$

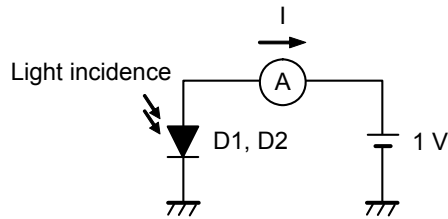


Figure 24

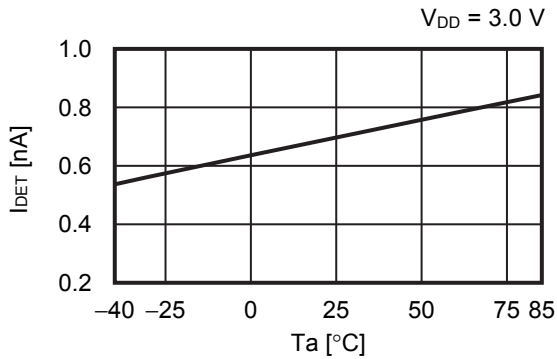
- Caution 1.** Select PD or LED after thorough evaluation with actual application. ABLIC Inc. shall not take responsibility for operation and characteristics of PD or LED.
- 2.** As for the circuit of detecting photocurrent difference, shown in Figure 22 and Figure 23, use the two PDs or the two LEDs that have the same characteristics in generation voltage and in generation current, respectively.

■ Precautions

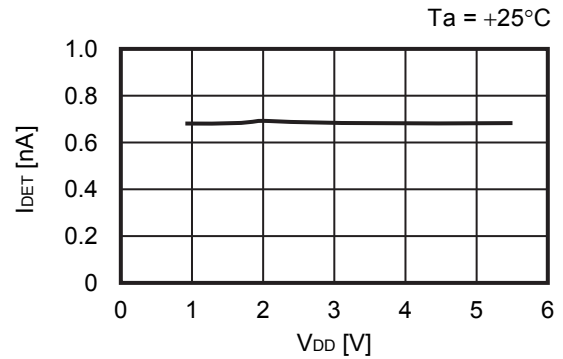
- Use the S-5470 Series with the output current of 20 mA or less.
- The S-5470 Series may malfunction if the power supply voltage changes suddenly.
- As for the detecting circuit of the photocurrent difference (Refer to "**Figure 22, Figure 23 Example Photocurrent Level Difference Detector**"), use the S-5470 Series when input current of INP pin is 20 μ A or less and input current of INM pin is 10 μ A or less. In case of input current excess, note that the S-5470 Series might malfunction.
- The output in the S-5470 Series is unstable in lower voltage than the minimum operation voltage. At the time of power-on, use the S-5470 Series after output stabilization.
- Set a capacitor of 0.1 μ F or more between the VDD pin and VSS pin for stabilization.
- Since INP pin and INM pin is easy to be affected by disturbance noise, perform countermeasures such as mounting external parts to ICs as close as possible.
- If power impedance is high, the S-5470 Series may malfunction due to voltage drop caused by feed-through current. Set wire patterns carefully for lower power impedance.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- ABLIC Inc. claims no responsibility for any disputes arising out of or in connection with any infringement by products including this IC of patents owned by a third party.

■ Characteristics (Typical Data)

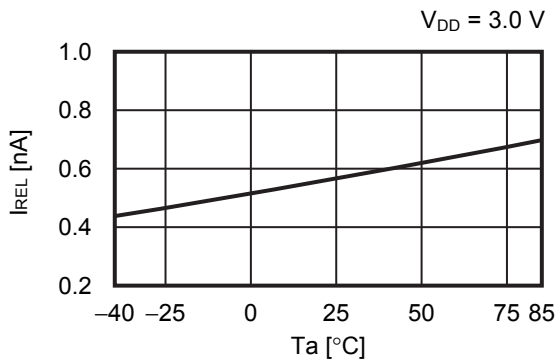
1. Detection current vs. Temperature



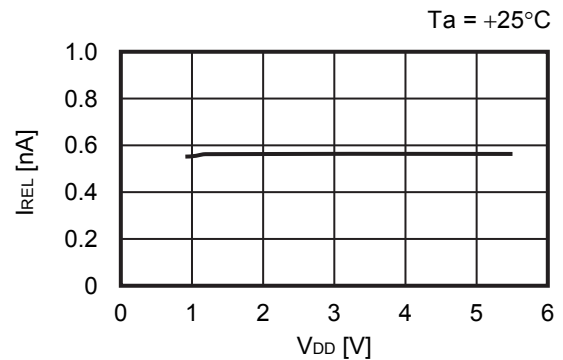
2. Detection current vs. Power supply voltage



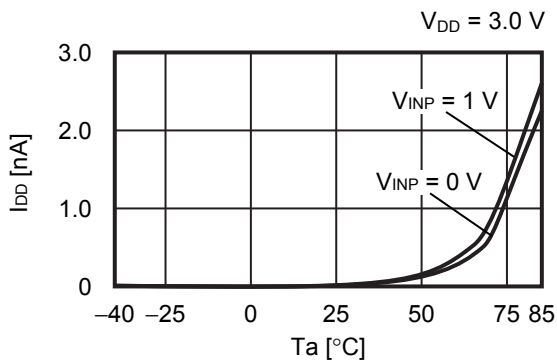
3. Release current vs. Temperature



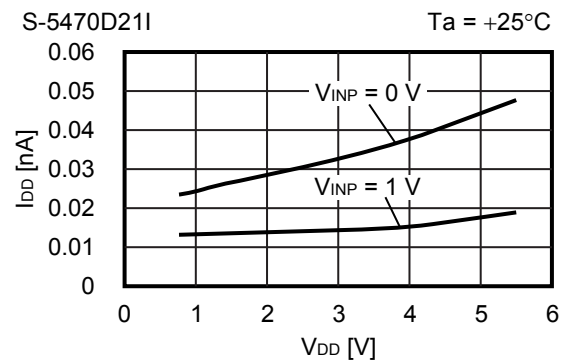
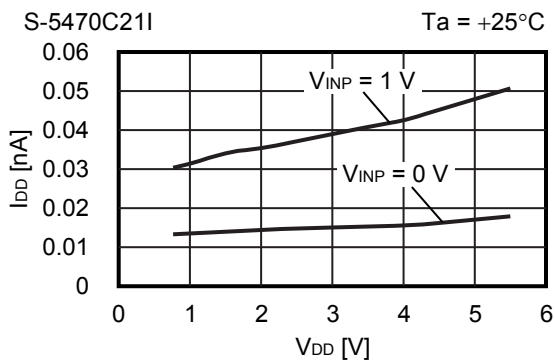
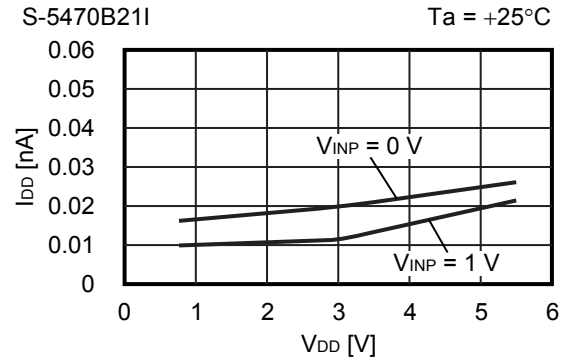
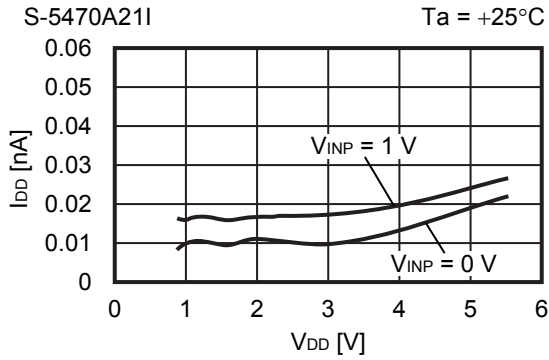
4. Release current vs. Power supply voltage



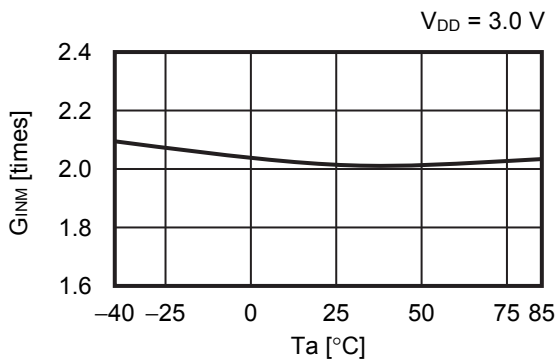
5. Current consumption vs. Temperature



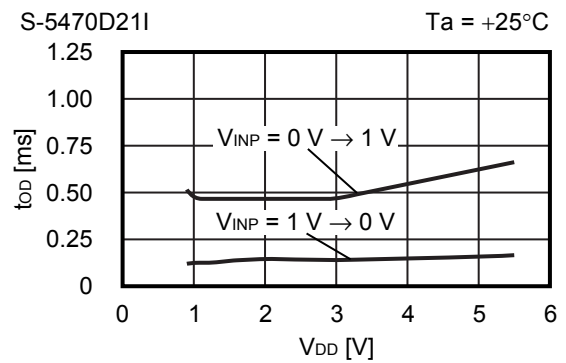
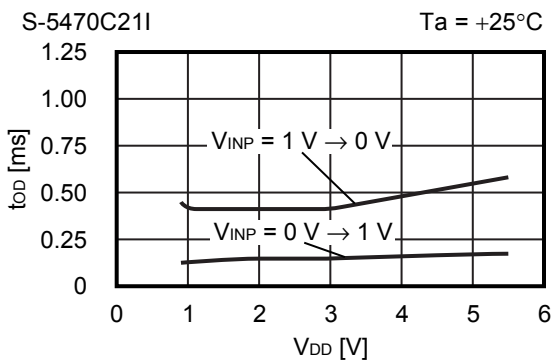
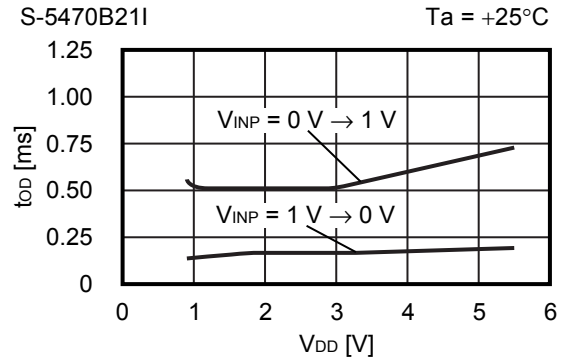
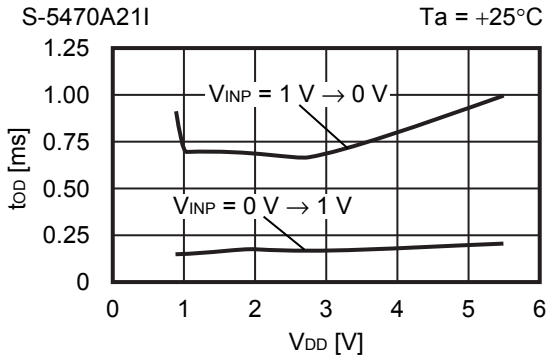
6. Current consumption vs. Power supply



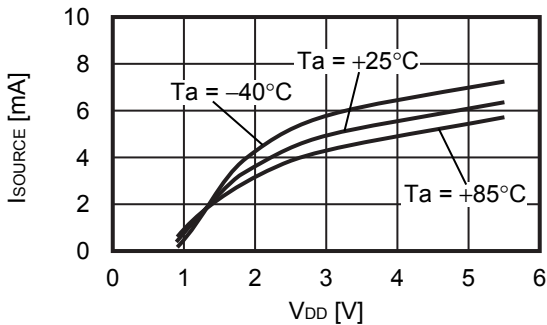
7. Current amplifier current amplification ratio vs. Temperature



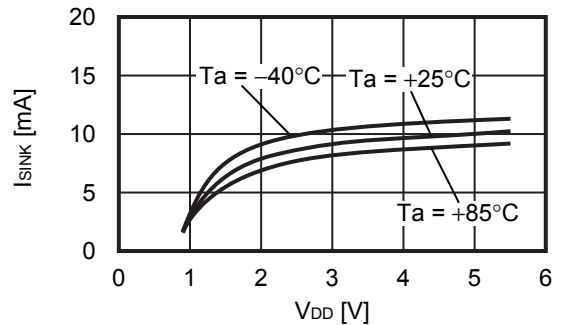
8. Output response time vs. Power supply voltage



9. Source current vs. Power supply voltage

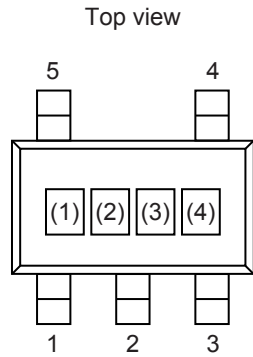


10. Sink current vs. Power supply voltage



■ **Marking Specification**

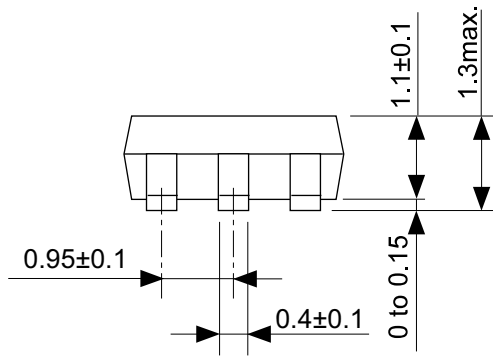
1. **SOT-23-5**



(1) to (3): Product code (Refer to **Product name vs. Product code**)
 (4): Lot number

Product name vs. Product code

Product Name	Product Code		
	(1)	(2)	(3)
S-5470A21I-M5T1U	Y	H	A
S-5470B21I-M5T1U	Y	H	I
S-5470C21I-M5T1U	Y	H	Q
S-5470D21I-M5T1U	Y	H	Y



No. MP005-A-P-SD-1.3

TITLE	SOT235-A-PKG Dimensions
No.	MP005-A-P-SD-1.3
ANGLE	
UNIT	mm
ABLIC Inc.	



Feed direction →

No. MP005-A-C-SD-2.1

TITLE	SOT235-A-Carrier Tape
No.	MP005-A-C-SD-2.1
ANGLE	
UNIT	mm
ABLIC Inc.	



Enlarged drawing in the central part



No. MP005-A-R-SD-1.1

TITLE	SOT235-A-Reel		
No.	MP005-A-R-SD-1.1		
ANGLE		QTY.	3,000
UNIT	mm		
ABLIC Inc.			

Disclaimers (Handling Precautions)

1. All the information described herein (product data, specifications, figures, tables, programs, algorithms and application circuit examples, etc.) is current as of publishing date of this document and is subject to change without notice.
2. The circuit examples and the usages described herein are for reference only, and do not guarantee the success of any specific mass-production design.
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by the reasons other than the products described herein (hereinafter "the products") or infringement of third-party intellectual property right and any other right due to the use of the information described herein.
3. ABLIC Inc. is not liable for any losses, damages, claims or demands caused by the incorrect information described herein.
4. Be careful to use the products within their ranges described herein. Pay special attention for use to the absolute maximum ratings, operation voltage range and electrical characteristics, etc.
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by failures and / or accidents, etc. due to the use of the products outside their specified ranges.
5. Before using the products, confirm their applications, and the laws and regulations of the region or country where they are used and verify suitability, safety and other factors for the intended use.
6. When exporting the products, comply with the Foreign Exchange and Foreign Trade Act and all other export-related laws, and follow the required procedures.
7. The products are strictly prohibited from using, providing or exporting for the purposes of the development of weapons of mass destruction or military use. ABLIC Inc. is not liable for any losses, damages, claims or demands caused by any provision or export to the person or entity who intends to develop, manufacture, use or store nuclear, biological or chemical weapons or missiles, or use any other military purposes.
8. The products are not designed to be used as part of any device or equipment that may affect the human body, human life, or assets (such as medical equipment, disaster prevention systems, security systems, combustion control systems, infrastructure control systems, vehicle equipment, traffic systems, in-vehicle equipment, aviation equipment, aerospace equipment, and nuclear-related equipment), excluding when specified for in-vehicle use or other uses by ABLIC, Inc. Do not apply the products to the above listed devices and equipments.
ABLIC Inc. is not liable for any losses, damages, claims or demands caused by unauthorized or unspecified use of the products.
9. In general, semiconductor products may fail or malfunction with some probability. The user of the products should therefore take responsibility to give thorough consideration to safety design including redundancy, fire spread prevention measures, and malfunction prevention to prevent accidents causing injury or death, fires and social damage, etc. that may ensue from the products' failure or malfunction.
The entire system in which the products are used must be sufficiently evaluated and judged whether the products are allowed to apply for the system on customer's own responsibility.
10. The products are not designed to be radiation-proof. The necessary radiation measures should be taken in the product design by the customer depending on the intended use.
11. The products do not affect human health under normal use. However, they contain chemical substances and heavy metals and should therefore not be put in the mouth. The fracture surfaces of wafers and chips may be sharp. Be careful when handling these with the bare hands to prevent injuries, etc.
12. When disposing of the products, comply with the laws and ordinances of the country or region where they are used.
13. The information described herein contains copyright information and know-how of ABLIC Inc. The information described herein does not convey any license under any intellectual property rights or any other rights belonging to ABLIC Inc. or a third party. Reproduction or copying of the information from this document or any part of this document described herein for the purpose of disclosing it to a third-party is strictly prohibited without the express permission of ABLIC Inc.
14. For more details on the information described herein or any other questions, please contact ABLIC Inc.'s sales representative.
15. This Disclaimers have been delivered in a text using the Japanese language, which text, despite any translations into the English language and the Chinese language, shall be controlling.

2.4-2019.07

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

[ABLIC:](#)

[S-5470A21I-M5T1U](#) [S-5470D21I-M5T1U](#) [S-5470B21I-M5T1U](#) [S-5470C21I-M5T1U](#)

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9